



Session Title:	[MD2] Plasma-Surface Interaction
Session Date:	November 20 (Mon.), 2023
Session Time:	14:55-16:40
Session Room:	Room D (Grand Ballroom 3, 2F)
Session Chair	Prof. Remi Dussart (GREMI Univ. of Orleans CNRS, France)

[MD2-1] 14:55-15:15

Improvement of Mass Transfer Characteristics in Si_3N_4 Etching in H_3PO_4 Solution for 3D NAND Manufacturing

Taegun Park, Jongwon Han, and Sangwoo Lim (Yonsei Univ., Korea)

[MD2-2] 15:15-15:35

Plasma Process Switching from Deposition to Etching in Ar/ C_4F_8 Plasma by N_2 Addition

Woojin Park, Jonggu Han, and Se Youn Moon (Jeonbuk Nat'l Univ., Korea)

[MD2-3] 15:35-15:55

Cryogenic Aspect Ratio Etching of SiO_2 at $\text{CF}_4/\text{H}_2/\text{Ar}$ Plasma

Hee Tae Kwon, In Young Bang, Jae Hyeon Kim, Hyeon Jo Kim, Seong Yong Lim, Seo Yeon Kim, Seong Hee Jo, Ji Hwan Kim, Woo Jae Kim, Gi Won Shin, and Gi-Chung Kwon (Kwangwoon Univ., Korea)

[MD2-4] [Plenary] 15:55-16:40

Low Temperature Plasma-Materials Interactions for Plasma Etching

Gottlieb S. Oehrlein (Univ. of Maryland, USA)